30. (Amended) A semiconductor device having an active matrix type display device, said display device comprising:

a substrate having an insulating surface;

a plurality of pixel electrodes arranged in a matrix formed over said substrate;

a plurality of first thin film transistors for switching said pixel electrodes and formed over said substrate;

a driver circuit formed over said substrate for driving said plurality of first thin film transistors, said driver circuit comprising at least one second thin film transistor;

each of said first thin film transistors and said second thin film transistor comprising:

a semiconductor film comprising silicon and including at least one channel region;

a gate insulating film adjacent to said channel region; and

a gate electrode adjacent to said gate insulating film;

wherein the semiconductor film of said second thin film transistor contains germanium at a higher concentration that the semiconductor film of said first thin film transistors and the semiconductor film of the first thin film transistors is not intentionally added with germanium.

31. (Amended) The semiconductor device according to claim 30 wherein the semiconductor film of said plurality of fist thin film transistors is not added with germanium while the semiconductor film of said second thin film transistor is added with germanium.

33. (Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a first thin film transistor formed over said substrate, said first thin film transistor comprising:

a first semiconductor film comprising crystalline silicon formed over said substrate and having a channel region;

a first gate insulating film adjacent to said first semiconductor film; and

a first gate electrode adjacent to said first gate insulating film;

a second thin film transistor formed over said substrate, said second thin film transistor comprising:

a second semiconductor film comprising crystalline silicon formed over said substrate and having a channel region;

a second gate insulating film adjacent to said second semiconductor film; and

a second gate electrode adjacent to said second gate insulating film;

wherein said first semiconductor film contains germanium at a higher concentration than sad second semiconductor film and the second semiconductor film is not intentionally added with germanium.

34. (Amended) The semiconductor device according to claim 33 wherein said first semiconductor film is added with germanium while the second semiconductor film is not intentionally added with germanium.

36. (Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a first thin film transistor formed over said substrate, said first thin film transistor comprising:

a first semiconductor film comprising crystalline silicon formed over said substrate and having a channel region;

a first gate insulating film adjacent to said first semiconductor film; and

a first gate electrode adjacent to said first gate insulating film;

a second thin film transistor formed over said substrate, said second thin film transistor comprising:

a second semiconductor film comprising amorphous silicon formed over said substrate and having a channel region;

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a second gate insulating film adjacent to said second semiconductor film; and

a second gate electrode adjacent to said second gate insulating film,

wherein said first semiconductor film contains germanium at a higher concentration than said second semiconductor film and the second semiconductor film is not intentionally added with germanium.

37. (Amended) The semiconductor device according to claim 36 wherein said first semiconductor film is added with germanium while the second semiconductor film is not intentionally added with germanium.

Please cancel Claims 3, 6, 9, 12 and 15.

Please add the following new Claims 39-43:

39. (New) The semiconductor device according to claim 1 wherein the first active layer further comprises a metal selected from the group consisting of nickel, iron, cobalt, and platinum.

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40. (New) The semiconductor device according to claim 2 wherein the first active layer further comprises a metal selected from the group consisting of nickel, iron, cobalt, and platinum.